## What is claimed:

- 1. A positive photoresist composition comprising a photoactive component and a polymer that comprises 1) groups reactive to crosslinking; and 2) photoacid-labile groups.
- 2. The photoresist of claim/1 wherein groups 1) comprise acetal groups or ester groups.
  - 3. The photoresist of claim 1 wherein groups 1) comprise acetal groups.
- 4. The photoresist of claim 3 wherein the acetal group have an oxygen linkage that is substituted by a secondary or tertiary carbon.
- 5. The photoresist of claim 3 or 4 wherein the polymer comprises units of the following Formula I:

I

wherein W is a linker group;

R is an optionally substituted cyclic or non-cyclic alkyl group;

R1 is hydrogen or a cyclic or non-cyclic alkyl group;

Y is hydrogen or optionally substituted alkyl.

- 6. The photoresist of any one of claims 1 through 5 wherein the polymer comprises phenolic units.
- 7. The photoresist of any one of claims 1 through 6 wherein the polymer comprises cycloalkyl units.

- 8. The photoresist of claim 1 wherein the polymer comprises alkyl acrylate photoacid labile groups.
- 9. A positive photoresist composition comprising a photoactive component and a component that comprises groups reactive to crosslinking, and a component that comprises photoacid-labile groups.
- 10. The photoresist of claim 9 wherein the component with crosslinking groups and the component with photoacid labile groups are a single component of the photoresist.
- 11. The photoresist of claim 9 wherein the component with crosslinking groups and the component with photoacid-labile groups are separate components of the photoresist.
- 12. The photoresist of claim 10 or 11 wherein the crosslinking groups are acetal groups.
- 13. The photoresist of claim 12 wherein the acetal group have an oxygen linkage that is substituted/by a secondary or tertiary carbon.
- 14. The photoresist of any one of claims 1 through 13 wherein the polymer is substantially free of aromatic groups.
- 15. The photoresist of any one of claims 1 through 14 wherein the photoresist comprises a thermal acid generator compound.
- 16. The photoresist of any one of claims 1 through 14 wherein the photoresist is free of a thermal acid generator compound.

- A method for treating a microelectronic wafer substrate, comprising: 17.
- applying a layer of a photoresist composition of any one of claims 1 through a) 16 on the microelectronic substrate; and
- exposing and developing the photoresist layer on the substrate to yield a developed photoresist layer;
- thermally treating the developed photoresist layer to induce crosslinking of c) one or more photoresist components.
  - The method of claim 17 wherein the substrate is a microelectronic wafer. 18.
- 19. The method of claim 17 or 18 wherein the photoresist layer is exposed to patterned radiation having a wavelength of about 248 nm.
- The method of claim 17 or 18 wherein the photoresist layer is exposed to 20. patterned radiation having a wavelength of less than 200 nm.
- 21. The method of any one of claims 17 through 20 wherein the thermal treatment induces flow of the developed photoresist layer.
- 22. The method of any one of claims 17 through 21 wherein the substrate comprises one or more contact holes.
- 23. The method of claim 22 wherein the photoresist layer flows into the one or more contact holes during the thermal treatment.
- 24. The method of any one of claims 17 through 23 wherein the photoresist layer is heated after development to at least about 130°C.
- 25. The method of any one of claims 17 through 23 wherein the photoresist layer is heated after development to at least about 150°C.

- 26. The method of any one of claims 17 through 23 wherein the photoresist layer is heated after development to at least about 160°C.
- 27. The method of any one of claims 17 through 26 wherein the photoresist is heated after exposure and prior to development at a temperature of not greater than about 120°C, and the pre-development heating does not cause substantial crosslinking of the photoresist layer.
- 28. An article of manufacture comprising a substrate having coated thereon a photoresist composition of any one of claims 1 through 16.
  - 29. An arficle of claim 28 wherein the substrate is a microelectronic wafer.
- 30. An article of claim 28 wherein the microelectronic wafer comprises one or more contact holes.

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